# TMA16xP Series

# Triac (Bidirectional Triode Thyristor)

### **Selection Guide**

| Part Number | V <sub>DRM</sub><br>(V) | Package                    | Packing            |
|-------------|-------------------------|----------------------------|--------------------|
| TMA164P-L   | 400                     | 3-pin SIP with exposed pad | 30 pieces per tube |
| TMA166P-L   | 600                     | for heatsink mount         | so pieces per tube |

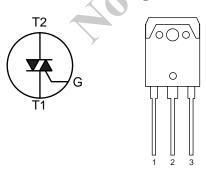
#### **Absolute Maximum Ratings**

| Characteristic                         | Symbol              |   | Notes   | Rating     | Units             |
|--|---------------------|---|---|------------|-------------------|
| Dook Donotitivo Off State Valtage      | V <sub>DRM</sub>    | TMA164P-L   |   | 400        | V                 |
| Peak Repetitive Off-State Voltage      |                     | TMA166P-L   | R <sub>GREF</sub> = ∞                             | 600        | V                 |
| Deals Non Depatitive Off State Valtage | V <sub>DSM</sub>    | TMA164P-L   | R <sub>GREF</sub> = ∞                             | 500        | V                 |
| Peak Non-Repetitive Off-State Voltage  |                     | TMA166P-L   |   | 700        | V                 |
| RMS On-State Current                   | I <sub>T(RMS)</sub> | 50/60 Hz full c<br>total Conduction<br>$T_C = 108^{\circ}C$             | 16  | A          |                   |
|  | I <sub>TSM</sub>    | f = 60 Hz   | Full cycle sine wave, peak value, non-repetitive, | 190        | A                 |
| Surge On-State Current                 |                     | f = 50 Hz   | initial T <sub>J</sub> = 125°C                    | 180        | A                 |
| I <sup>2</sup> t Value for Fusing      | l²t                 | Value for 50 Hz half cycle sine wave, 1 cycle, I <sub>TSM</sub> = 180 A |   | 160        | A <sup>2</sup> •s |
| Peak Gate Current                      | I <sub>GM</sub>     | f ≥ 50 Hz, duty cycle ≤ 10%   |   | 2          | A                 |
| Peak Gate Power Dissipation            | P <sub>GM</sub>     | f ≥ 50 Hz, duty cycle ≤ 10%   |   | 5          | W                 |
| Average Gate Power Dissipation         | P <sub>GM(AV)</sub> | T <sub>J</sub> < T <sub>J</sub> (max)                                   |   | 0.5        | W                 |
| Junction Temperature                   | TJ                  |   |   | -40 to 125 | °C                |
| Storage Temperature                    | T <sub>stg</sub>    |   |   | -40 to 125 | °C                |

#### Thermal Characteristics May require derating at maximum conditions

| Characteristic                                   | Symbol           | Test Conditions | Value | Units |
|--|------------------|-----------------|-------|-------|
| Package Thermal Resistance<br>(Junction to Case) | R <sub>0JC</sub> | For AC          | 1.0   | °C/W  |

# Pin-out Diagram



# Terminal List Table Number Name Function 1 T1 Main terminal, gate referenced

| 1 | 11 | Main terminal, gate referenced       |
|---|----|--------------------------------------|
| 2 | T2 | Main terminal connect to signal side |
| 3 | G  | Gate control                         |

All performance characteristics given are typical values for circuit or system baseline design only and are at the nominal operating voltage and an ambient temperature,  $T_A$ , of 25°C, unless otherwise stated.





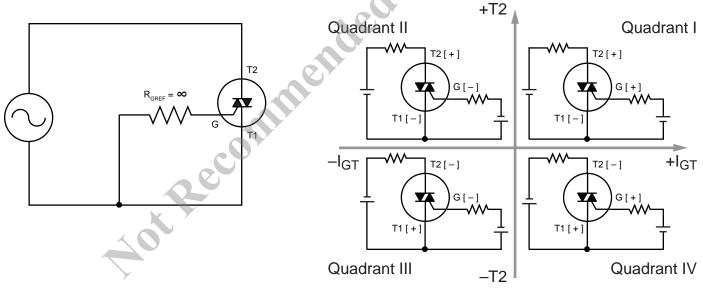
# **ELECTRICAL CHARACTERISTICS**

| Characteristics   | Symbol           | Test Conditions   |   | Min. | Тур. | Max. | Unit |
|---|------------------|---|---|------|------|------|------|
| Off State Lealers Comment   |                  | $V_D = V_{DRM}$ , $T_J = 125^{\circ}C$ , $R_{GREF} = \infty$ using test circuit 1 |   |      | _    | 2.0  | mA   |
| Off-State Leakage Current   | I <sub>DRM</sub> | $V_D = V_{DRM}, T_J = 25^{\circ}C,$   | _   | _    | 100  | μA   |      |
| On-State Voltage  | V <sub>TM</sub>  | I <sub>T</sub> = 20 A, T <sub>J</sub> = 25°C                                      | _   | _    | 1.4  | V    |      |
|   |                  | Quadrant I: T2+, G+   | $V_D = 12 V, R_L = 20 \Omega, T_J = 25^{\circ}C$                    | -    | -    | 1.5  | V    |
| Gate Trigger Voltage  | V <sub>GT</sub>  | Quadrant II: T2+, G-  |   | -    | -    | 1.5  | V    |
|   |                  | Quadrant III: T2–, G–   |   | -    |      | 1.5  | V    |
|   |                  | Quadrant I: T2+, G+   | V <sub>D</sub> = 12 V, R <sub>L</sub> = 20 Ω, T <sub>J</sub> = 25°C | -    |      | 30   | mA   |
| Gate Trigger Current  | I <sub>GT</sub>  | Quadrant II: T2+, G-  |   | - 6  |      | 30   | mA   |
|   |                  | Quadrant III: T2–, G–   |   | -0   | 7 -  | 30   | mA   |
| Gate Non-trigger Voltage  | V <sub>GD</sub>  | $V_D = V_{DRM} \times 0.5, R_L = 4$   | 0.2   | -    | -    | V    |      |
| Critical Rising Rate of<br>Off-State Voltage during<br>Commutation* | (dv/dt)c         | $T_J = 125^{\circ}C, V_D = 400 V, (di/dt)c = -8 A/ms, I_{TP} = 2 A$ 10            |   |      | -    | -    | V/µs |

\*Where  $I_{TP}$  is the peak current through T2 to T1.

# **Test Circuit 1**

# Gate Trigger Characteristics

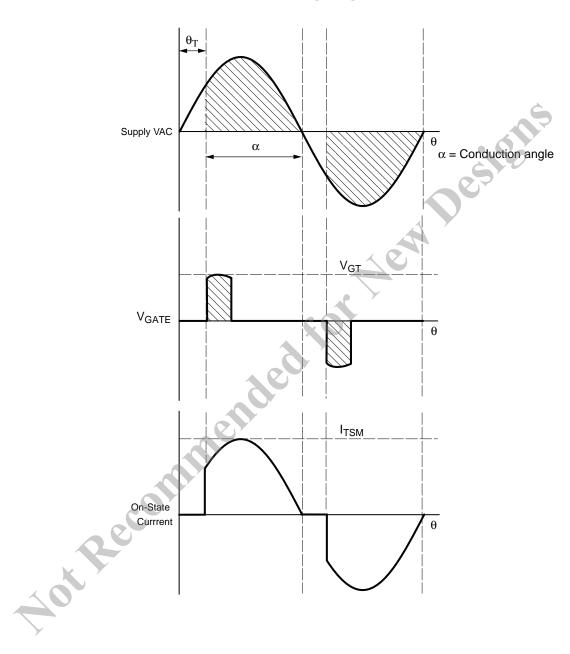


Polarities referenced to T1



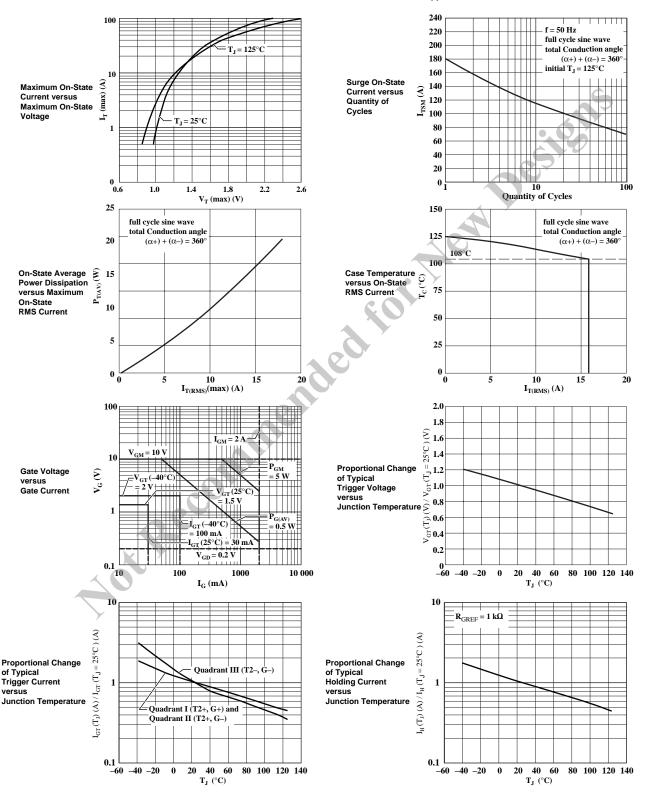


# **Commutation Timing Diagrams**





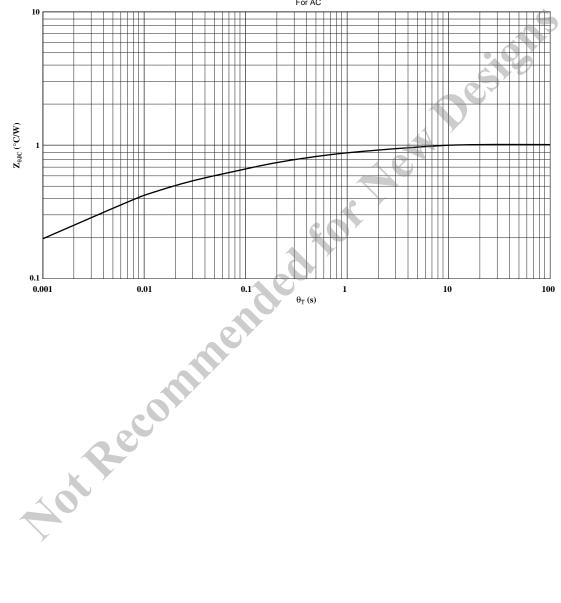




Performance Characteristics at T<sub>A</sub> = 25°C



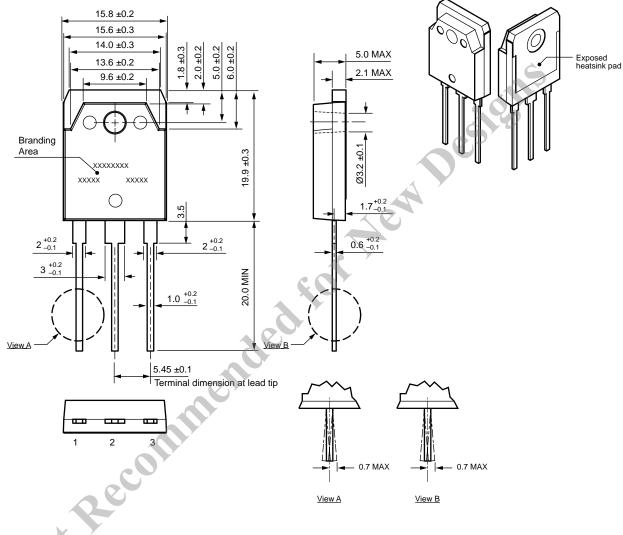




#### Transient Thermal Impedence versus Triac Voltage Pulse Duration For AC







### **TO-3P Package Outline Drawing**

Gate burr: 0.3 mm (max.), mold flash may appear at opposite side Terminal core material: Cu Terminal treatment: Ni plating and Pb-free solder dip

Leadform: 100 Package: TO-3P (M100)

Dimensions in millimeters

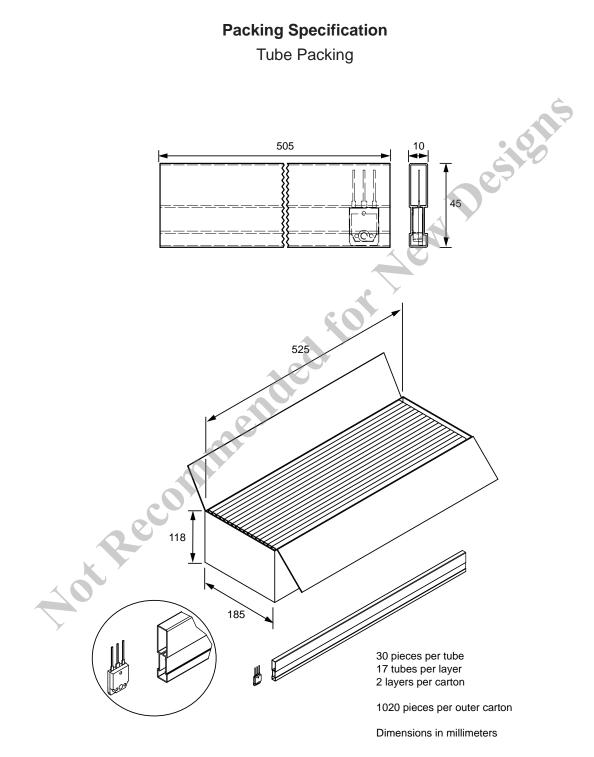
Branding codes (exact appearance at manufacturer discretion): 1st line, type: MA16xP 2nd line left, lot: YM Where: Y is the last digit of the year of manufacture M is the month (1 to 9, O, N, D) 2nd line right, subtype: L



Leadframe plating Pb-free. Device meets RoHS requirements.

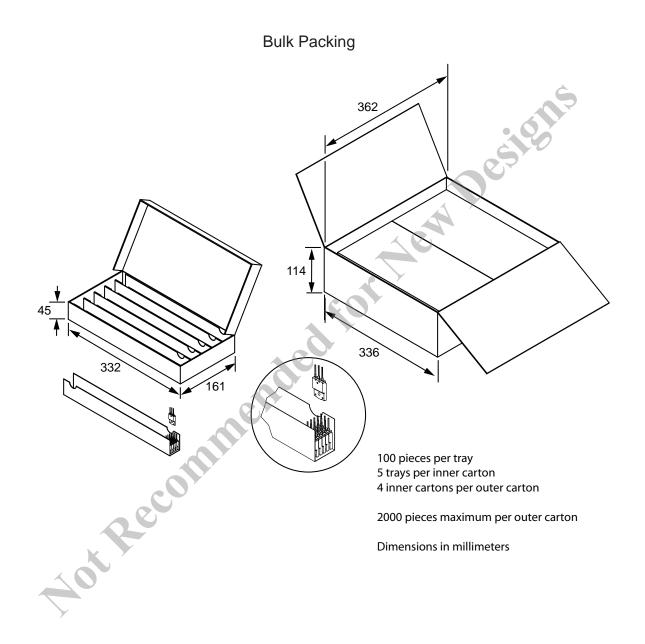


















WARNING — These devices are designed to be operated at lethal voltages and energy levels. Circuit designs that embody these components must conform with applicable safety requirements. Precautions must be taken to prevent accidental contact with power-line potentials. Do not connect grounded test equipment.

The use of an isolation transformer is recommended during circuit development and breadboarding.

Because reliability can be affected adversely by improper storage environments and handling methods, please observe the following cautions.

#### **Cautions for Storage**

- Ensure that storage conditions comply with the standard temperature (5°C to 35°C) and the standard relative humidity (around 40 to 75%); avoid storage locations that experience extreme changes in temperature or humidity.
- Avoid locations where dust or harmful gases are present and avoid direct sunlight.
- Reinspect for rust on leads and solderability of products that have been stored for a long time.

#### **Cautions for Testing and Handling**

When tests are carried out during inspection testing and other standard test periods, protect the products from power surges from the testing device, shorts between adjacent products, and shorts to the heatsink.

#### Remarks About Using Silicone Grease with a Heatsink

- When silicone grease is used in mounting this product on a heatsink, it shall be applied evenly and thinly. If more silicone grease than required is applied, it may produce stress.
- Coat the back surface of the product and both surfaces of the insulating plate to improve heat transfer between the product and the heatsink.
- Volatile-type silicone greases may permeate the product and produce cracks after long periods of time, resulting in reduced heat radiation effect, and possibly shortening the lifetime of the product.
- Our recommended silicone greases for heat radiation purposes, which will not cause any adverse effect on the product life, are indicated below:

| Туре   | Suppliers                            |
|--------|--------------------------------------|
| G746   | Shin-Etsu Chemical Co., Ltd.         |
| YG6260 | Momentive Performance Materials      |
| SC102  | Dow Corning Toray Silicone Co., Ltd. |

#### **Heatsink Mounting Method**

- Torque When Tightening Mounting Screws. Thermal resistance increases when tightening torque is low, and radiation effects are decreased. When the torque is too high, the screw can strip, the heatsink can be deformed, and distortion can arise in the product frame. To avoid these problems, observe the recommended tightening torques for this product package type 0.686 to 0.882 N•m (7 to 9 kgf•cm).
- Diameter of Heatsink Hole: < 4 mm. The deflection of the press mold when making the hole may cause the case material to crack at the joint with the heatsink. Please pay special attention for this effect.

#### Soldering

When soldering the products, please be sure to minimize the working time, within the following limits:

260±5°C 10 s

350±5°C 3 s

• Soldering iron should be at a distance of at least 1.5 mm from the body of the products

#### **Electrostatic Discharge**

- When handling the products, operator must be grounded. Grounded wrist straps worn should have at least 1 M $\Omega$  of resistance to ground to prevent shock hazard.
- Workbenches where the products are handled should be grounded and be provided with conductive table and floor mats.
- When using measuring equipment such as a curve tracer, the equipment should be grounded.
- When soldering the products, the head of soldering irons or the solder bath must be grounded in other to prevent leak voltages generated by them from being applied to the products.
- The products should always be stored and transported in our shipping containers or conductive containers, or be wrapped in aluminum foil.





Fortempester

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